

# Product Manual

EKWIN ELECTRONICS CO.,LTD

**EK BT151**

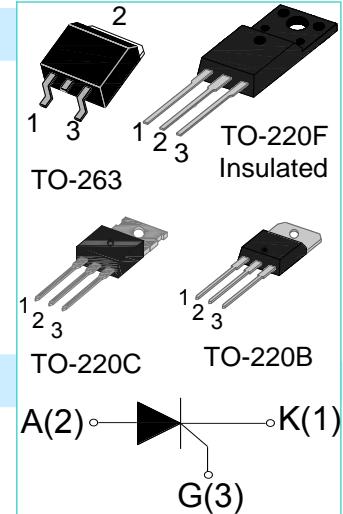
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**12A SCRs**
**BT151 Serial**
**Main Features:**

<b>IT(RMS)</b>	<b>VDRM/VRRM</b>	<b>VTM</b>
12 A	600V and 800 V	$\leq 1.7$ V

**Description:**

High current density due to singel mesa technology.BT151 series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. BT151 series are suitable for general purpose applications.a high gate sensitivity is required .


**Absolute Ratings(limiting values) :**

<b>Symbol</b>	<b>Parameter</b>		<b>value</b>	<b>Unit</b>	
<b>I<sub>T(RMS)</sub></b>	on-state RMS current(180°C conduction angle)		TO-220B/C TO-263 (T <sub>c</sub> =100°C) TO-220F(T <sub>c</sub> =85°C)	12	A
<b>I<sub>TSM</sub></b>	Non repetitive surge peak on-state current (T <sub>j</sub> = 25 °C)		tp= 8.3 ms	110	A
			tp = 10 ms	100	
<b>V<sub>DRM</sub></b>	Repetitive peak off-state voltage(T <sub>j</sub> =25 °C)		600 and 800	V	
<b>V<sub>RMM</sub></b>	Repetitive peak reverse voltage(T <sub>j</sub> =25 °C)		600 and 800	V	
<b>T<sub>stg</sub> T<sub>j</sub></b>	Storage and operating junction temperature range		- 40 to + 150 - 40 to + 125	°C	
<b>I<sup>2</sup>t</b>	I <sup>2</sup> t value for fusing T <sub>j</sub> = 125°C	tp = 10 ms	50	A <sup>2</sup> s	
<b>dI/dt</b>	Critical rate of rise of on-state current I <sub>G</sub> =2xI <sub>GT</sub> , tr≤100ns		50	A/μs	
<b>IGM</b>	Peak gate current tp=20us T <sub>j</sub> =125 °C		2	A	
<b>PGM</b>	Peak gate power tp=20us T <sub>j</sub> =125 °C		5	W	
<b>PG(av)</b>	Average gate power dissipation T <sub>j</sub> =125 °C		0.5	W	

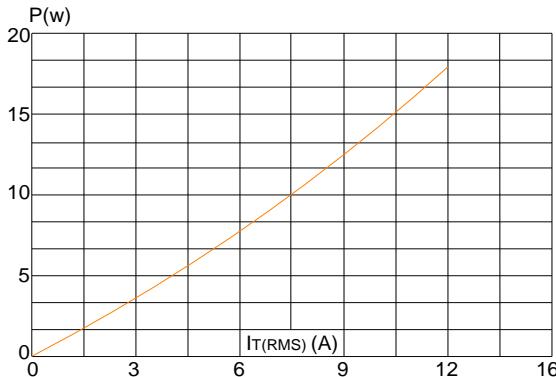
### Electrical Characteristics :

Symbol	Test Condition		range	Value	Unit
<b>I<sub>GT</sub></b>	V <sub>D</sub> =12V      R <sub>L</sub> =3.3kΩ	T <sub>j</sub> =25°C	MAX	15	mA
<b>V<sub>GT</sub></b>		T <sub>j</sub> =25°C	MAX	1.5	V
<b>V<sub>GD</sub></b>	V <sub>D</sub> =V <sub>DRM</sub> R <sub>L</sub> =3.3kΩ	T <sub>j</sub> =125°C	MIN	0.2	V
<b>t<sub>gt</sub></b>	V <sub>D</sub> =V <sub>DRM</sub> I <sub>G</sub> = 500mA    dI <sub>G</sub> /dt = 0.2A/μs	T <sub>j</sub> =25°C	TYP	2	μs
<b>I<sub>L</sub></b>	V <sub>D</sub> =12V    I <sub>GT</sub> = 0.1 A	T <sub>j</sub> =25°C	TYP	40	mA
<b>I<sub>H</sub></b>	I <sub>T</sub> = 500mA gate open	T <sub>j</sub> =25°C	MAX	30	mA
<b>V<sub>TM</sub></b>	I <sub>TM</sub> = 2*I <sub>T</sub> (RMS)    tp=380μs	T <sub>j</sub> =25°C	MAX	1.7	V
<b>I<sub>DRM</sub> I<sub>RRM</sub></b>	V <sub>D</sub> =V <sub>DRM</sub> , V <sub>R</sub> =V <sub>RRM</sub>	T <sub>j</sub> =125°C	TYP	10	μA
		T <sub>j</sub> =125°C	MAX	0.5	mA
<b>dV<sub>D</sub>/dt</b>	V <sub>D</sub> =67%V <sub>DR</sub> exponential waveform; R <sub>GK</sub> = 100 Ω	T <sub>j</sub> =125°C	TYP	200	V/μs

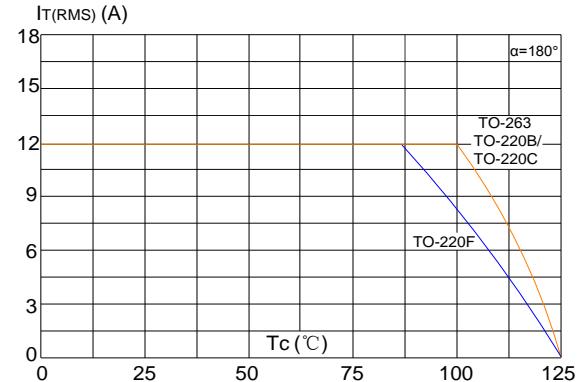
### Thermal Resistances :

Symbol	Parameter	Value	Unit
<b>R<sub>th (j-mb)</sub></b>	Thermal resistance from junction to mounting case	TO-220F	4.5
		TO-220B/C   TO-263	2.4
			°C/W

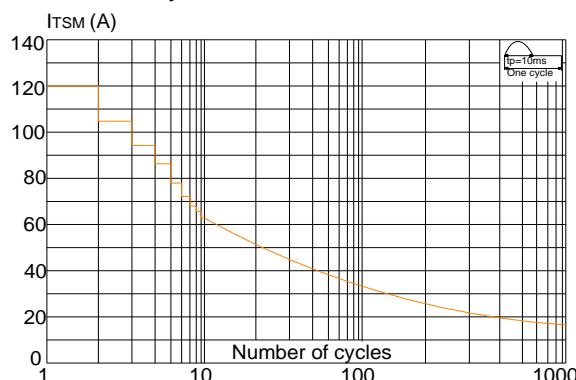
**FIG.1:** Maximum power dissipation versus RMS on-state current



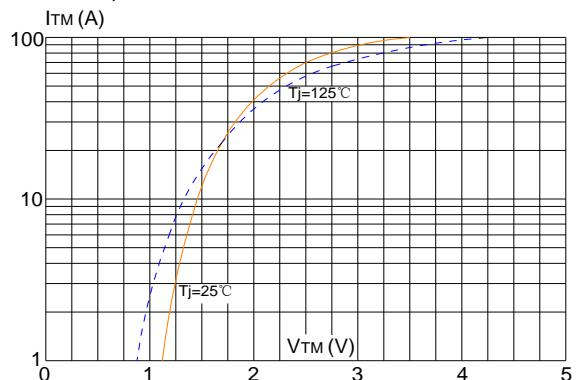
**FIG.2:** RMS on-state current versus case temperature



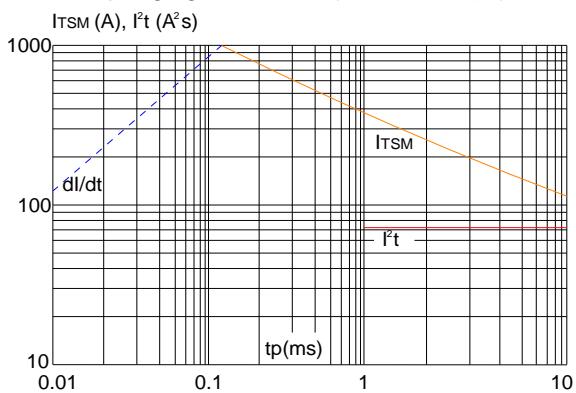
**FIG.3:** Surge peak on-state current versus number of cycles



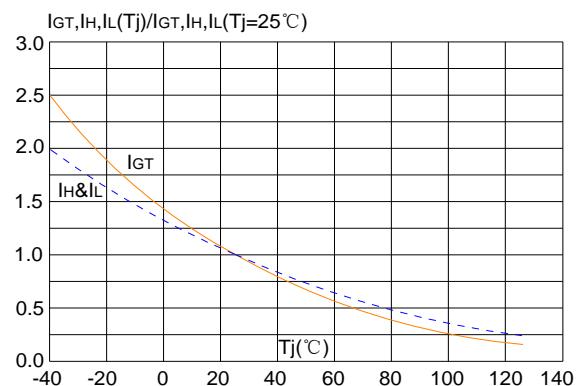
**FIG.4:** On-state characteristics (maximum values)



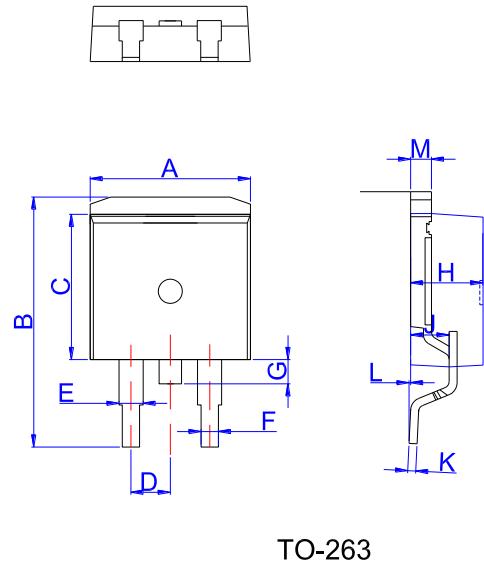
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $tp < 10\text{ms}$ , and corresponding value of  $I^2t$  ( $dI/dt < 50\text{A}/\mu\text{s}$ )



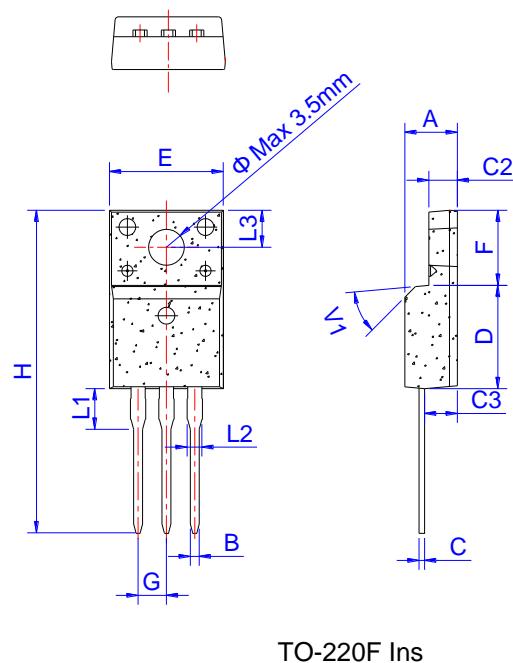
**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature



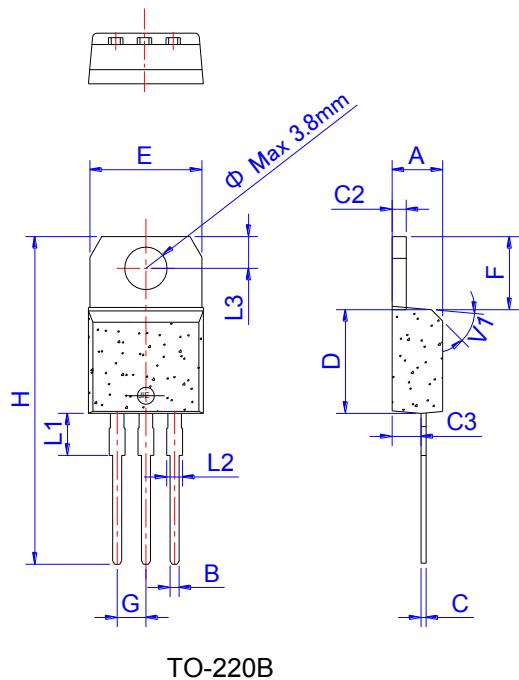
### Package Mechanical Data :



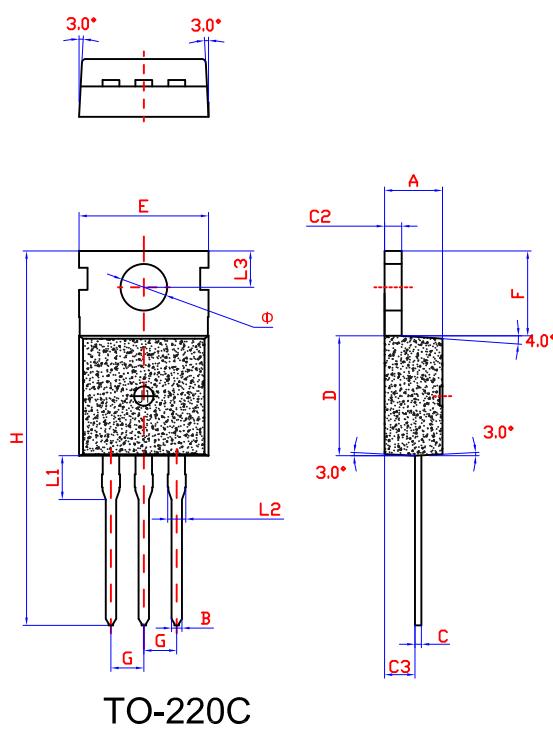
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90		10.20	0.390		0.402
B	14.70		15.80	0.579		0.622
C	9.4		9.6	0.37		0.378
D		2.54			0.100	
E	1.20		1.40	0.047		0.055
F	0.75		0.85	0.029		0.033
G			1.75			0.069
H	4.40		4.70	0.173		0.185
J	2.30		2.70	0.091		0.106
K	0.38		0.55	0.015		0.022
L	0	0.10	0.25	0	0.004	0.010
M	1.25		1.35	0.049		0.053



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.80	0.173		0.189
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.48		0.75	0.019		0.030
C2	2.40		2.70	0.094		0.106
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.70		10.3	0.382		0.406
F	6.40		7.00	0.252		0.276
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
I		3.63			0.143	
J	1.14		1.70	0.045		0.067
K		3.30			0.130	
V1		45°			45°	



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.60		10.4	0.378		0.409
F	6.20		6.60	0.244		0.260
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.4		4.6	0.173		1.181
B	0.7		0.9	0.027		0.035
C	0.45		0.6	0.018		0.024
C2	1.23		1.32	0.048		0.052
C3	2.2		2.6	0.086		0.102
D	8.9		9.9	0.350		0.390
E	9.9		10.3	0.390		0.406
F	6.3		6.9	0.248		0.272
G		2.54			0.1	
H	28.0		29.8	11.0		11.7
L1		3.2			0.126	
L2	1.14		1.7	0.045		0.067
L3	2.65		2.95	0.104		0.116
Φ		3.6			0.142	